

Lecture-14

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- MOS Differential Pair Small Signal Analysis
- Differential Pair with Common Mode Input
- Examples

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Lecture 13 - Review

Quantitative Analysis – differential input





Lecture 13 - Review

Quantitative Analysis – differential input



Linearity of a differential pair can be improved by decreasing W/L and/or increasing I_{ss}



Lecture 13 - Review

Quantitative Analysis – differential input

• The equilibrium overdrive (i.e, when M_1 and M_2 are drawing equal portion of I_{ss}) is given by:





MOS Differential Pair – small signal analysis

<u>Quantitative Analysis – differential input</u>

• From large signal analysis we achieved:

$$\therefore |A_{v}| = \frac{V_{out1} - V_{out2}}{\Delta V_{in}} = \left(\mu_{n}C_{ox}\frac{W}{L}I_{SS}R_{D} \right)$$

At equilibrium, this is g_{m}

• How to arrive at this result using small signal analysis?

 $\therefore |A_{v}| = \frac{V_{out1} - V_{out2}}{\Delta V_{in}} = g_{m}R_{D}$

- Two techniques
 - Superposition method
 - Half-circuit concept



MOS Differential Pair – small signal analysis

 We apply small signals to V_{in1} and V_{in2} and assume M₁ and M₂ are already operating in saturation.





MOS Differential Pair – small signal analysis

- <u>Method-I</u>: Superposition technique in this the idea is to see the effect of V_{in1} and V_{in2} on the overall output and then combine them to get the differential small signal voltage gain
- First set, V_{in2} = 0
- Then let us calculate V_X/V_{in1}





MOS Differential Pair – small signal analysis

• Superposition technique





MOS Differential Pair – small signal analysis

- Superposition technique
 - Now calculate V_y/V_{in1} ۲



Thevenin Equivalent Circuit

analysis





MOS Differential Pair – small signal analysis

- Superposition technique
 - Now combine the expressions to calculate small signal voltage only due to V_{in1}



- The magnitude of differential gain is g_mR_D regardless of how the inputs are applied
- The gain will be halved if single ended output is considered



MOS Differential Pair – small signal analysis

- Half Circuit Approach
 - If a fully symmetric differential pair senses differential inputs (i.e, the two inputs change by equal and opposite amounts from the equilibrium condition), then the concept of half circuit can be applied.



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-V_{in1}

MOS Differential Pair – small signal analysis

Half Circuit Approach



We can write:

$$\frac{V_X}{V_{in1}} = -g_m R_D \qquad \qquad \frac{V_Y}{-V_{in1}} = -g_m R_D$$

Therefore the differential output can be expressed as:

$$V_X - V_Y = 2V_{in1} \left(-g_m R_D\right)$$

Thus the small signal voltage given is:

$$A_{v} = \frac{V_{X} - V_{Y}}{2V_{in1}} = -g_{m}R_{D}$$

MOS Differential Pair – small signal analysis

- How does the gain of a differential amplifier compare with a CS stage?
 - For a given total bias current I_{SS} , the value of equivalent g_m of a differential pair is $1/\sqrt{2}$ times that of g_m of a single transistor biased at the I_{SS} with the same dimensions. Thus the total gain is proportionally less.
 - Equivalently, for given device dimensions and load impedance, a differential pair achieves the same gain as a CS stage at the cost of twice the bias current.
- What is the advantage of differential stage then?
 - Definitely the noise suppression capability. Right?



MOS Differential Pair – small signal analysis

• How is gain affected if channel length modulation is considered?





MOS Differential Pair – small signal analysis

 The virtual ground on the source allows division of two identical CS amplifiers: → differential half circuits



$$V_X = -g_m V_{in1} \left(R_D \parallel r_o \right)$$

$$V_{Y} = g_{m} V_{in1} \left(R_{D} \parallel r_{o} \right)$$

$$\Rightarrow V_X - V_Y = -g_m (2V_{in1}) (R_D \parallel r_o)$$

$$\therefore A_{v} = \frac{V_{X} - V_{Y}}{2V_{in1}} = -g_{m} (R_{D} || r_{o})$$

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Small signal analysis – asymmetric inputs





Small signal analysis – asymmetric inputs



If the circuit is fully symmetric and I_{SS} is ideal current source, then M_1 and M_2 draws half of I_{SS} and is independent of $V_{in,CM}$. The V_x and V_y experience no change as $V_{in,CM}$ varies. In essence, the circuit simply amplifies the difference between V_{in1} and V_{in2} while eliminating the effect of $V_{in,CM}$.



MOS Differential Pair – Common Mode Response

Quantitative Analysis

- In ideal condition, differential pair has the ability to suppress variations in the common-mode voltage
- However, in practical scenarios there is always some CM output

<u>Case-I</u>: differential pair is symmetric but the current source has finite output impedance.





MOS Differential Pair – Common Mode Response (contd.)

 Shorting of X and Y brings M₁ and M₂ in parallel → they share all of their respective terminals



Thus the finite output impedance of the tail current source results in some common-mode gain in a symmetric differential pair

In addition, input CM variations also limit the output voltage swings

MOS Differential Pair – Common Mode Response (contd.)

Case-II: Effect of input common-mode variation when there is mismatch in R_D and the differential pair suffers from finite output impedance of current source.



- What happens to V_X and V_Y as $\Rightarrow R_D + \Delta R_D$ • What happens to V_X and V_Y as $V_{in,CM}$ increases? • Since M_1 and M_2 are symmetric
 - Since M_1 and M_2 are symmetric $\rightarrow I_{D1}$ and I_{D2} increases by same amount:

$$\Delta I_D = \frac{g_m}{1 + 2g_m R_{SS}} \Delta V_{in,CM}$$

• The respective change in V_x and V_y are given by:

$$\Delta V_{X} = -\Delta V_{in,CM} \frac{g_{m}}{1 + 2g_{m}R_{SS}} R_{D}$$

$$\Delta V_{Y} = -\Delta V_{in,CM} \frac{g_{m}}{1 + 2g_{m}R_{SS}} (R_{D} + \Delta R_{D})$$



MOS Differential Pair – Common Mode Response (contd.)

• Therefore the differential output due to mis-matched R_D is:

$$\Rightarrow \Delta V_X - \Delta V_Y = -\Delta V_{in,CM} \left[\frac{g_m}{1 + 2g_m R_{SS}} R_D - \frac{g_m}{1 + 2g_m R_{SS}} R_D - \frac{g_m}{1 + 2g_m R_{SS}} \Delta R_D \right]$$
$$\therefore \Delta V_X - \Delta V_Y = \left(\frac{g_m}{1 + 2g_m R_{SS}} \Delta R_D \right) \Delta V_{in,CM}$$

 It is apparent that a small common-mode input can generate a differential mode output → usually denoted by a metric called A_{CM-DM}

$$A_{CM-DM} = \frac{\Delta V_X - \Delta V_Y}{\Delta V_{in,CM}} = \frac{g_m}{1 + 2g_m R_{SS}} \Delta R_D$$



MOS Differential Pair – Common Mode Response (contd.)

Thus a common-mode input introduces a differential component, when the load is mis-matched, at the output

circuit exhibits common-mode to differential conversion

if the input of a differential pair includes both a differential signal and common-mode noise, the output is corrupted version of the input



Impact of common-mode to differential conversion

• With the increase in frequency of operation, the total capacitance (arising from the parasitics of the current source and the source-bulk junctions of M_1 and M_2) shunting the tail current source introduces larger tail current variations \rightarrow This large variation causes substantial common-mode to differential conversion even for very high output impedance of current source



Furthermore, The asymmetry due to load impedance mismatch (and hence the resulting common-mode to differential conversion) corrupts the amplified differential output



Impact of common-mode to differential conversion

- Summary: the common mode response of differential pairs depend on the output impedance of the tail current and the asymmetries in the circuit → manifestation of two effects
 - Variation of the output CM level (in the absence of mismatches)
 - Shifting of input common-mode variations to higher level at the output
- How about presence of mismatches?
 - Mismatches in R_D and mismatches in transistors (i.e, mismatches in transconductance)
 - The impact of transconductance mismatch on common-mode to differential conversion is more significant



Case-III: Effect of mismatches between M_1 and M_2 (dimension and V_T mismatches)

The asymmetry due to mismatch in the transistors generates slightly different currents in the two paths → leads to unequal transconductance



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Common-Mode Response (contd.)

$$V_{X} = V_{DD} - I_{D1}R_{D} = V_{DD} - g_{m1}(V_{in,CM} - V_{P})R_{D}$$

$$\Rightarrow V_X = V_{DD} - \frac{g_{m1}}{\left(g_{m1} + g_{m2}\right)R_{SS} + 1}R_D V_{in,CM}$$

$$\Rightarrow V_Y = V_{DD} - \frac{g_{m2}}{\left(g_{m1} + g_{m2}\right)R_{SS} + 1}R_D V_{in,CM}$$

$$\therefore V_{X} - V_{Y} = -\frac{g_{m1} - g_{m2}}{(g_{m1} + g_{m2})R_{SS} + 1}R_{D}V_{in,CM}$$

• The mismatch in the transistors convert the input CM variations to a differential error by a factor:

$$A_{CM-DM} = \frac{V_X - V_Y}{V_{in,CM}} = -\frac{\Delta g_m R_D}{\left(g_{m1} + g_{m2}\right)R_{SS} + 1}$$
 Unwanted



 Ideally, this unwanted A_{CM-DM} is normalized to the wanted A_{DM} → the normalization factor is called CMRR

$$CMRR = \left| \frac{A_{DM}}{A_{CM-DM}} \right|$$

 For a differential pair with mis-matched transistor but operating at equilibrium, the differential gain is given by:

$$|A_{DM}| = \frac{R_D}{2} \frac{g_{m1} + g_{m2} + 4g_{m1}g_{m2}R_{SS}}{1 + (g_{m1} + g_{m2})R_{SS}}$$
$$\Rightarrow CMRR = \left|\frac{A_{DM}}{A_{CM-DM}}\right| = \frac{g_{m1} + g_{m2} + 4g_{m1}g_{m2}R_{SS}}{2\Delta g_m} = \frac{g_m}{\Delta g_m} (1 + 2g_m R_{SS})$$

• Where, $g_m = (g_{m1} + g_{m2}) / 2$



Example – 1

- In the following circuit, $({}^{W}/{}_{L})_{1,2} = {}^{50}/{}_{0.5}$, $({}^{W}/{}_{L})_{3,4} = {}^{10}/{}_{0.5}$ and $I_{SS} = 0.5mA$. Also, I_{SS} is implemented with an NMOS having $({}^{W}/{}_{L})_{SS} = {}^{50}/{}_{0.5}$ while VDD =3V.
 - What are the minimum and maximum allowable input CM levels if the differential swings at the input and output are small.



Table 2.1 Level	1 SPICE Models	s for NMOS and PN	MOS Devices.
NMOS Model LEVEL = 1 NSUB = 9e+14 TOX = 9e-9 MJ = 0.45	VTO = 0.7 LD = 0.08e-6 PB = 0.9 MJSW = 0.2	GAMMA = 0.45 UO = 350 CJ = 0.56e-3 CGDO = 0.4e-9	PHI = 0.9 LAMBDA = 0.1 CJSW = 0.35e-11 JS = 1.0e-8
PMOS Model LEVEL = 1 NSUB = $5e+14$ TOX = $9e-9$ MJ = 0.5	VTO = -0.8 LD = 0.09e-6 PB = 0.9 MJSW = 0.3	GAMMA = 0.4 UO = 100 CJ = 0.94e-3 CGDO = 0.3e-9	PHI = 0.8 LAMBDA = 0.2 CJSW = 0.32e-11 JS = 0.5e-8

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Example – 1 (contd.)

$$I_{D1} = \frac{I_{SS}}{2} = 0.25 mA$$
 $(V_{OV})_1 = 0.193V$

$$(V_{in,CM})_{min} = V_{GS1} + (V_{OV})_{SS} = 0.7 + 0.193 + 0.273 = 1.17V$$

$$(V_{in,CM})_{max} = V_{DD} - |V_{GS3}| + V_{TN} \qquad |V_{GS3}| = |V_{TP}| + \sqrt{\frac{2I_{D3}}{\mu_p C_{ox} \left(\frac{W}{L}\right)_3}} = 1.61V$$

$$\therefore \left(V_{in,CM} \right)_{\text{max}} = 3 - 1.61 + 0.7 = 2.09V$$



Example – 2

- In the following circuit, $({}^{W}/{}_{L})_{1,2} = {}^{50}/{}_{0.5}$ and $R_{D} = 2k\Omega$. Suppose R_{SS} represents the output impedance on an NMOS current source with $({}^{W}/{}_{L})_{SS} = {}^{50}/{}_{0.5}$ and a drain current of 1mA. The input signal consists of $V_{in,DM} = 1.5V + V_n(t)$, where $V_n(t)$ denotes noise with a peak-to-peak amplitude of 100mV. Assume ${}^{\Delta R}/{}_{R} = 0.5\%$.
 - Calculate CMRR

